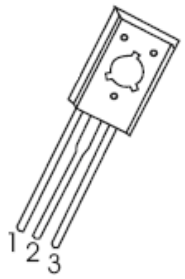
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126 Plastic-Encapsulate Transistors

BD234/236/238 TRANSISTOR (PNP)

TO-126



1. EMITTER
2. COLLECTOR
3. BASE

FEATURES

- Power Dissipation

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage	BD234	-45	V
		BD236	-60	
		BD238	-100	
V_{CEO}	Collector-Emitter Voltage	BD234	-45	V
		BD236	-60	
		BD238	-80	
V_{EBO}	Emitter-Base Voltage	BD234		V
		BD236	-5	
		BD238		
I_C	Collector Current –Continuous		-2	A
P_C	Collector Power Dissipation		1.25	W
T_J	Junction Temperature		150	℃
T_{stg}	Storage Temperature		-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	**BD234**	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-45		V
	BD236			-60		
	BD238			-100		
Collector-emitter breakdown voltage	**BD234**	$V_{(BR)CEO}$	I_C=-100mA,I_B=0	-45		V
	BD236			-60		
	BD238			-80		
Emitter-base breakdown voltage		$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5		V
Collector cut-off current	**BD234**	I_{CBO}	V_{CB}=-45V, I_E=0		-100	μA
	BD236		V_{CB}=-60V, I_E=0			
	BD238		V_{CB}=-100V, I_E=0			
Emitter cut-off current		I_{EBO}	V_{EB}=-5V, I_C=0		-1	mA
DC current gain		$h_{FE(1)}$	V_{CE}=-2V, I_C=-150mA	40		
		$h_{FE(2)}$	V_{CE}=-2V, I_C=-1A	25		
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=-1A, I_B=-100m A		-0.6	V
Transition frequency		f_T	V_{CE}=-10V, I_C=-250mA, f =10MHz	3		MHz